Docket No.: 60188-824 PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277

Hisashi NAKAYAMA, et al. : Confirmation Number:

Serial No.: : Group Art Unit:

Filed: March 25, 2004 : Examiner: Unknown

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

## INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The relevance of the references listed on attached Form 1449 is discussed in the present specification.

## Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Facsimile: (202) 756-8087 **Date: March 25, 2004** 

SHEET 1 OF 1

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						APPLICANT Hisashi NAKAYAMA, et al.						
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				U.S. PATE	NT	DOCUMENTS						
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Ok-Hyun NAM, et al., "Lateral Epitaxy of Low Defect Density GaN Layers Via Organometallic Vapor Phase Epitaxy", American Institute of Physics, Applied Physics Letters 71 (18), pp. 2638-2640, November 3, 1997												
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EXAMINER						DATE CONSIDERED						

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.